

<b>SANYO</b>	No.3204	2SD2117
	NPN Epitaxial Planar Silicon Transistor General Driver Applications	

**Features**

- Darlington connection
- High DC current gain
- Large current capacity, wide ASO

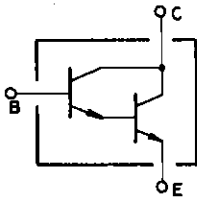
**Absolute Maximum Ratings at Ta = 25°C**

			unit
Collector to Base Voltage	V <sub>CB0</sub>	80	V
Collector to Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter to Base Voltage	V <sub>EBO</sub>	10	V
Collector Current	I <sub>C</sub>	1.5	A
Collector Current(Pulse)	I <sub>CP</sub>	3	A
Collector Dissipation	P <sub>C</sub>	1	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

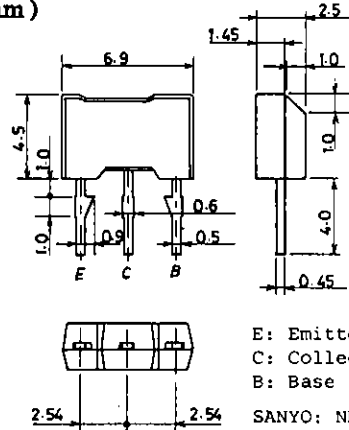
**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 40V, I <sub>E</sub> = 0			100	nA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = 6V, I <sub>C</sub> = 0			100	nA
DC Current Gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA	4000			
	h <sub>FE(2)</sub>	V <sub>CE</sub> = 2V, I <sub>C</sub> = 10mA	3000			
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 50mA		120		MHz
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 500mA, I <sub>B</sub> = 0.5mA		0.9	1.5	V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 500mA, I <sub>B</sub> = 0.5mA		1.5	2.0	V
C-B Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0	80			V
C-E Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, R <sub>BE</sub> = ∞	50			V
E-B Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0	10			V

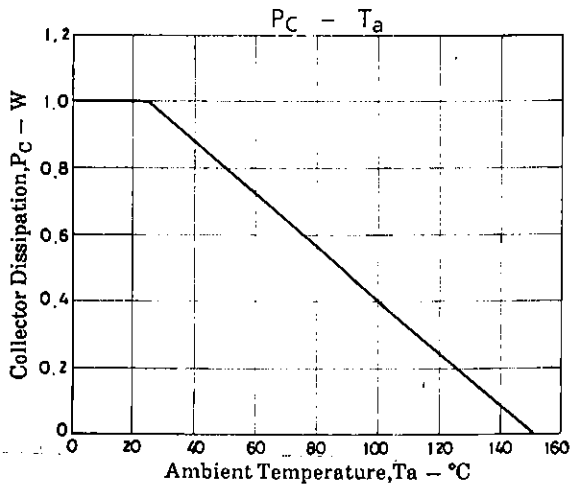
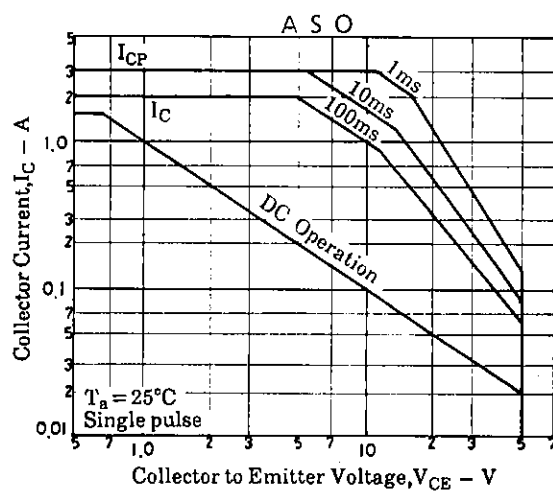
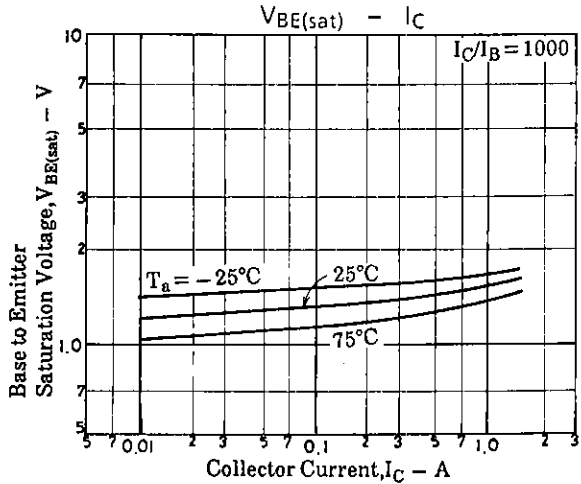
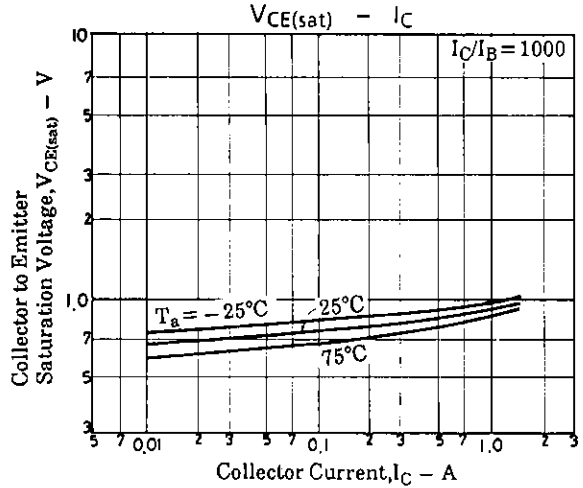
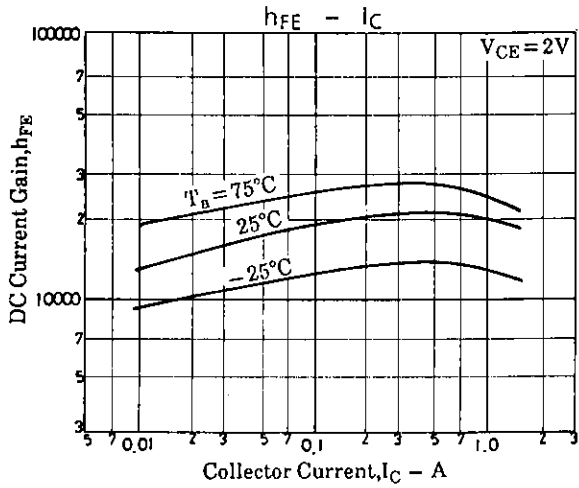
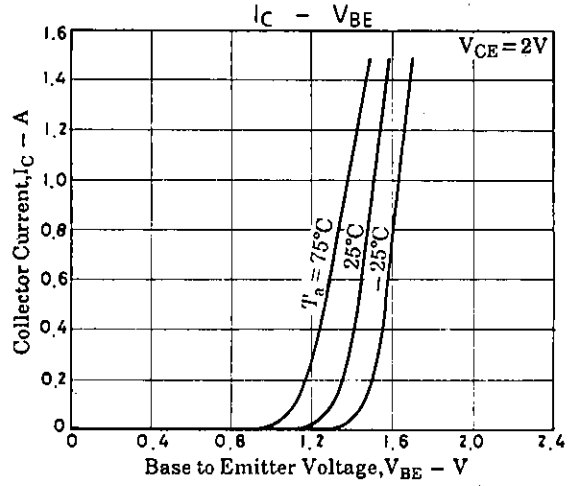
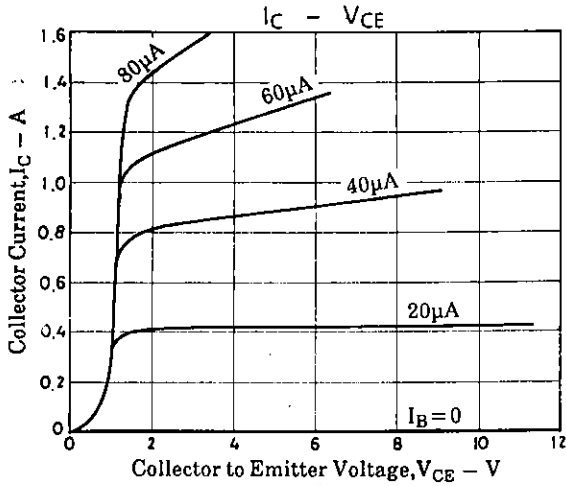
**Electrical Connection**



**Package Dimensions 2064**  
(unit: mm)



E: Emitter  
 C: Collector  
 B: Base  
 SANYO: NMP



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